

DIODE MODULE

DD(KD)100HB120/160

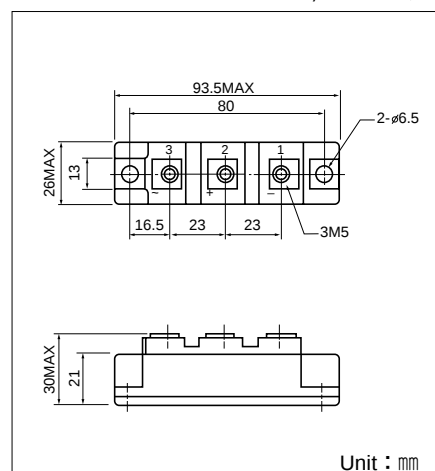
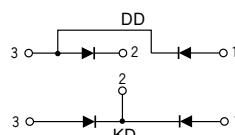
UL:E76102 (M)

Power Diode Module **DD100HB** series are designed for various rectifier circuits. **DD100HB** has two diode chips connected in series and the mounting base is electrically isolated from elements for simple heatsink construction. Wide voltage rating up to, 1,600V is available for various input voltage.

- Isolated mounting base
- Two elements in a package for simple (single and three phase) bridge connections
- Highly reliable glass passivated chips
- High surge current capability

(Applications)

Various rectifiers, Battery chargers, DC motor drives



Maximum Ratings

(T_j=25°C unless otherwise specified)

Symbol	Item	Ratings		Unit
		DD100HB120	DD100HB160	
V _{RRM}	Repetitive Peak Reverse Voltage	1200	1600	V
V _{RSM}	Non-Repetitive Peak Reverse Voltage	1350	1700	V

Symbol	Item		Conditions	Ratings	Unit
I _{F(AV)}	Average Forward Current		Single phase, half wave, 180° conduction, T _c : 111°C	100	A
I _{F(RMS)}	R.M.S. Forward Current		Single phase, half wave, 180° conduction, T _c : 111°C	155	A
I _{FSM}	Surge Forward Current		1/2 cycle, 50/60Hz, peak value, non-repetitive	1800/2000	A
I ² t	I ² t		Value for one cycle of surge current	16500	A²S
T _j	Junction Temperature			-40 to +150	°C
T _{stg}	Storage Temperature			-40 to +125	°C
V _{iso}	Isolation Voltage		A.C.1minute	2500	V
	Mounting Torque	Mounting (M6)	Recommended Value 2.5-3.9 (25-40)	4.7 (48)	N·m (kgf·cm)
		Terminal (M5)	Recommended Value 1.5-2.5 (15-25)	2.7 (28)	
	Mass			170	g

Electrical Characteristics

Symbol	Item	Conditions	Ratings	Unit
I _{RRM}	Repetitive Peak Reverse Current, max.	at V _{DRM} , single phase, half wave. T _j =150°C	30	mA
V _{FM}	Forward Voltage Drop, max.	Forward current 320A, T _j =25°C, Inst. measurement	1.35	V
R _{th(j-c)}	Thermal Impedance, max.	Junction to case	0.30	°C/W

